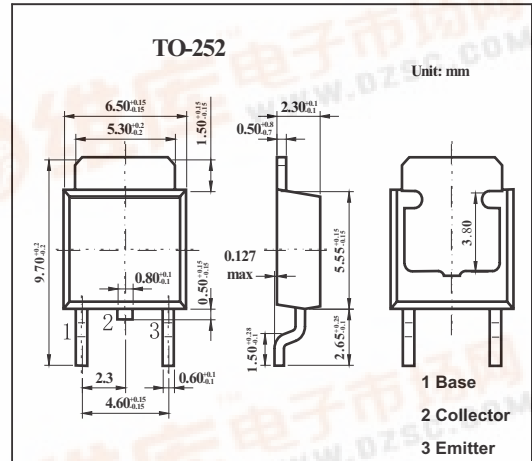


SMD Type Transistors

NPN Silicon Triple Diffused
2SC3233

Features

- Excellent Switching Times
tr=1.0μs (Max.) tf=1.0μs (Max.) at Ic=0.8A
- High collector Breakdown Voltage: VCEO=400V



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to base voltage	V _{CB0}	500	V
Collector to emitter voltage	V _{CEO}	400	V
Emitter to base voltage	V _{EBO}	7	V
Collector current	I _C	2	A
Base Current	I _B	0.5	A
Total Power dissipation Ta = 25°C Tc = 25°C	P _C	1	W
		20	W
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit	
collector cutoff current	I _{CBO}	V _{CB} =400V, I _E =0			100	μA	
emitter cutoff current	I _{EBO}	V _{EB} =7V, I _C =0			1	mA	
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =1mA, I _C =0	500			V	
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	400			V	
DC current Gain	h _{FE}	V _{CE} =5V, I _C =0.1A	20				
		V _{CE} =5V, I _C =1A	8				
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =0.1A, I _B =0.2A			1	V	
Base- Emitter Voltage	V _{BE(sat)}	I _C =0.1A, I _B =0.2A			1.5	V	
Switching time turn-On time	t _r				1.0	μs	
Switching storage time	t _{stg}					2.5	μs
	t _f					1	μs

